PECJ100P03A

Description

PECJ P-channel Enhancement Mode Power MOSFET

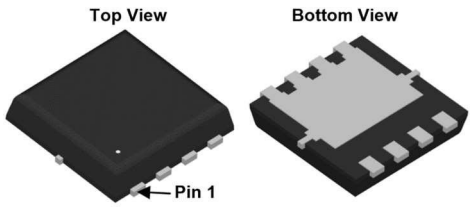
Features

- V_{DS} = -30V, I_D = -40A
  $R_{DS(ON)}$ < 10mΩ @ V_{GS} = -10V
  $R_{DS(ON)}$ < 16mΩ @ V_{GS} = -4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

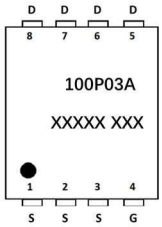
Application

- PWM Applications
- Load Switch
- Power Management

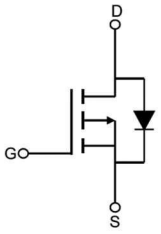
100% UIS TESTED!
100% ΔVds TESTED!



PDFN3.3X3.3-8L



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
Q100P03A	PECJ100P03A	TAPING	PDFN3.3X3.3-8L	13inch	5000	50,000

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	-40	A
		T_C = 100℃	-26	A
I_{DM}	Pulsed Drain Current note1		-160	A
E_{AS}	Single Pulsed Avalanche Energy note2		100	mJ
P_D	Power Dissipation	T_C = 25℃	25.6	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		4.9	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -30V, V_{GS}=0V	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.0	-1.6	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}= -10V, I_D= -20A	-	7.5	10	mΩ
		V_{GS}= -4.5V, I_D= -10A	-	11.6	16	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -15V, V_{GS}=0V, f=1.0MHz	-	3564	-	pF
C_{oss}	Output Capacitance		-	416	-	pF
C_{rss}	Reverse Transfer Capacitance		-	373	-	pF
Q_g	Total Gate Charge	V_{DS}= -15V, I_D= -20A, V_{GS}= -10V	-	37	-	nC
Q_{gs}	Gate-Source Charge		-	6.5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	9.4	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -15V, I_D= -20A, V_{GS}= -10V, R_{GEN}=2.5Ω	-	16	-	ns
t_r	Turn-on Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	68	-	ns
t_f	Turn-off Fall Time		-	52	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-40	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-160	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -30A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J= 25℃, V_{DD}= -15V, V_G= -10V, L= 0.5mH, R_G= 25Ω, I_{AS}= -20A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure1: Output Characteristics

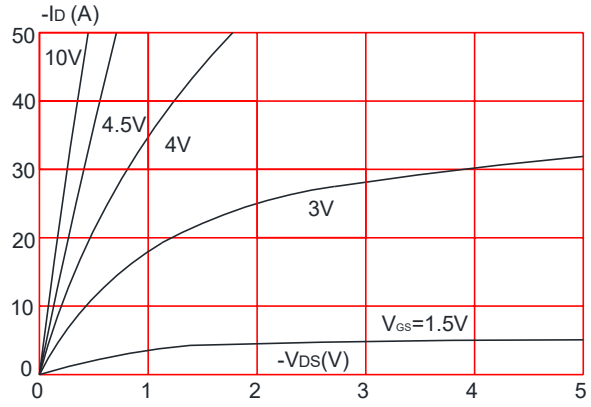


Figure 2: Typical Transfer Characteristics

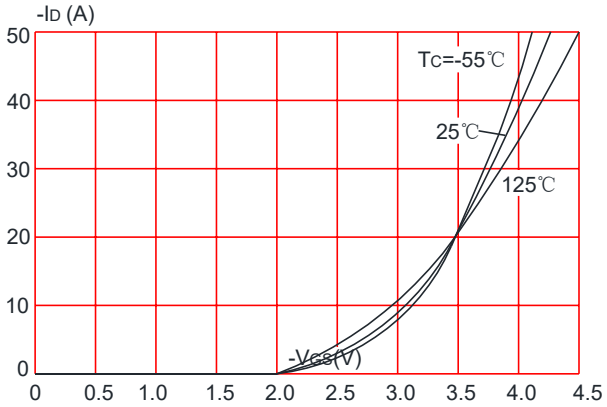


Figure 3: On-resistance vs. Drain Current

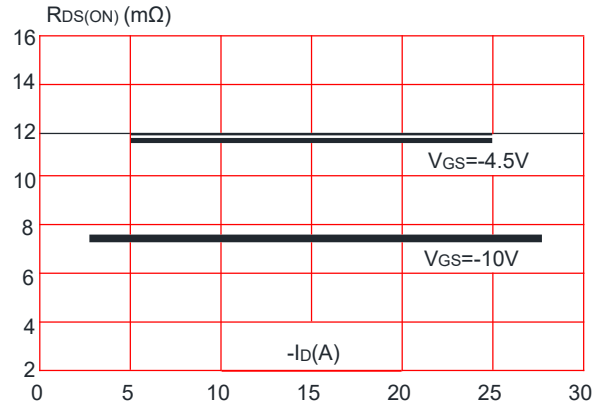


Figure 4: Body Diode Characteristics

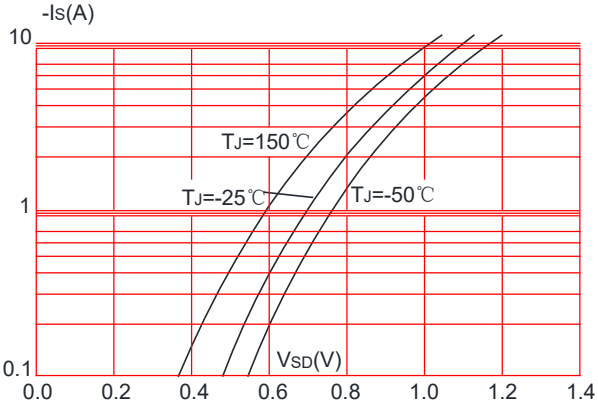


Figure 5: Gate Charge Characteristics

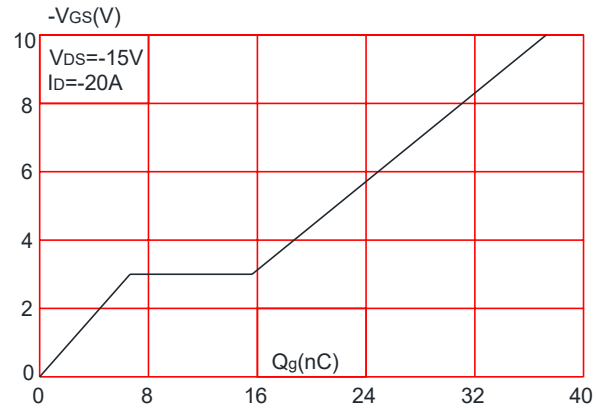


Figure 6: Capacitance Characteristics

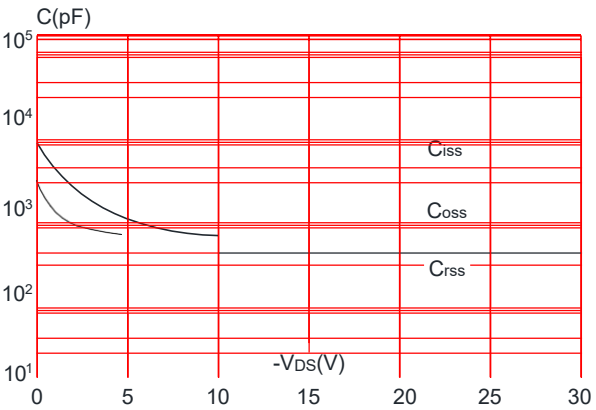


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

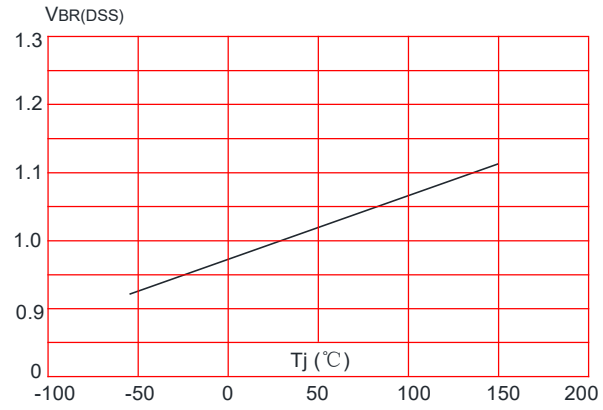


Figure 8: Normalized on Resistance vs. Junction Temperature

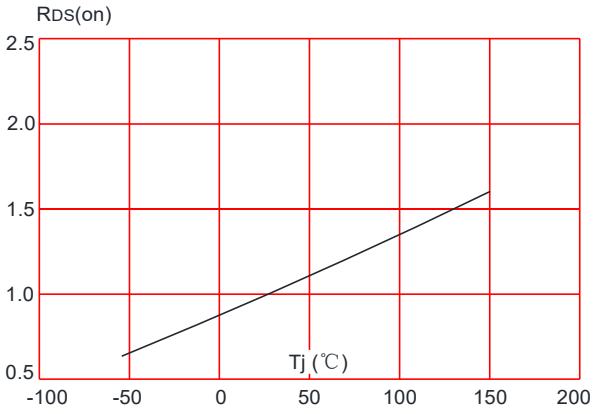


Figure 9: Maximum Safe Operating Area

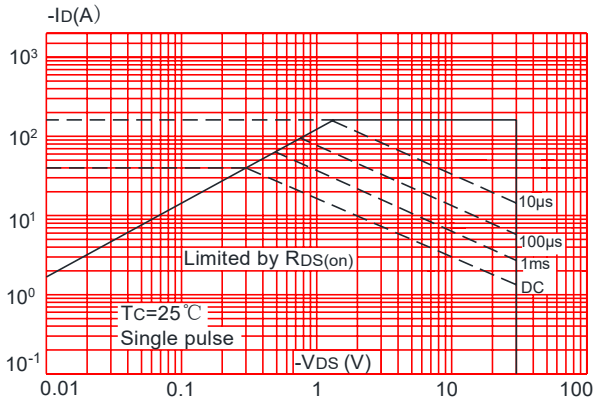


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

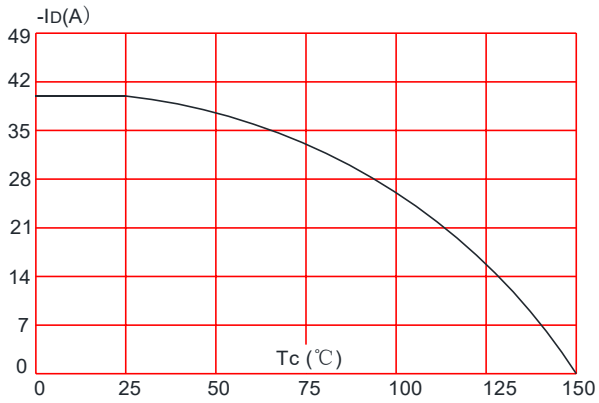
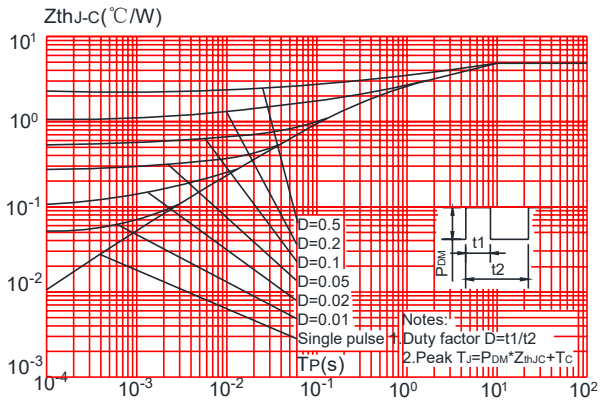
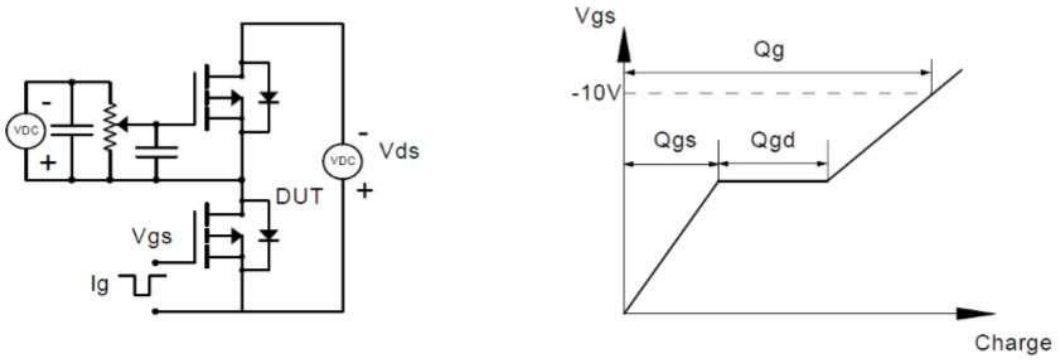


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

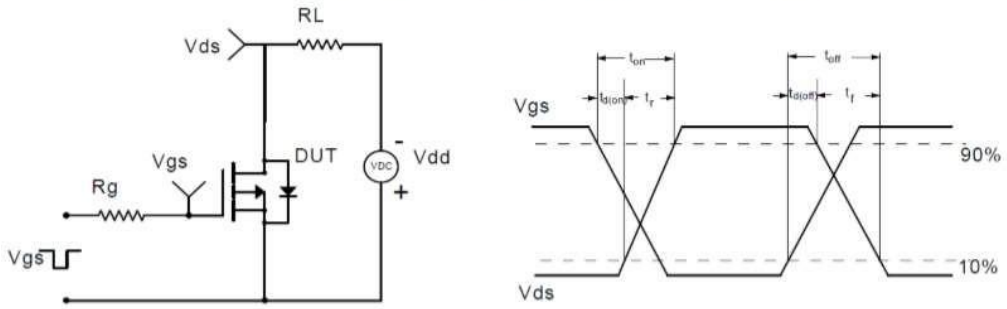


Test Circuit

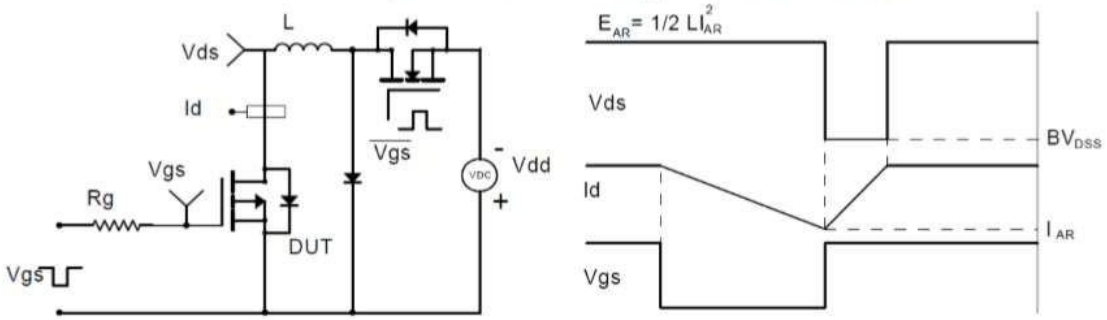
Gate Charge Test Circuit & Waveform



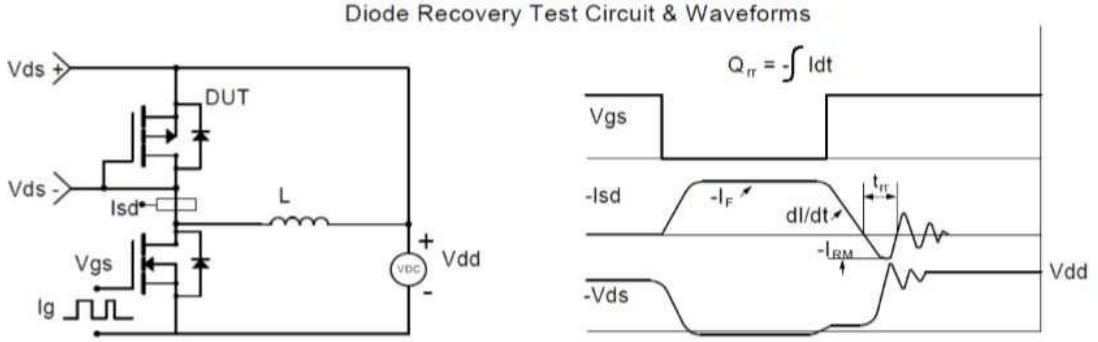
Resistive Switching Test Circuit & Waveforms



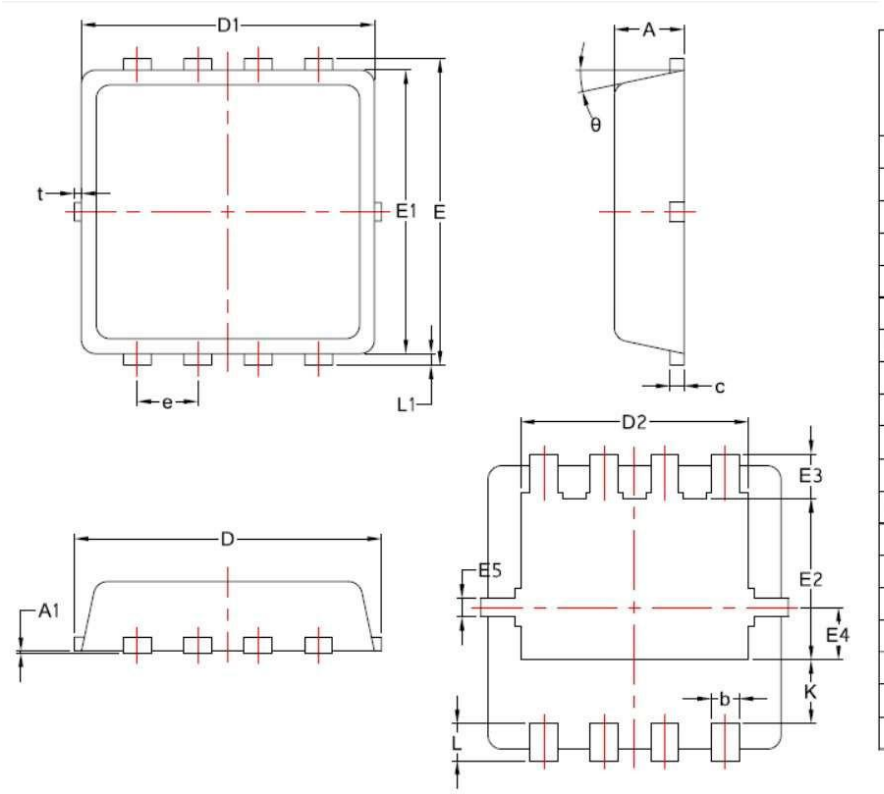
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Mechanical Data- PDFN3.3X3.3-8L



SYMBOL	COMMON		
	MM		
	MIN	NOM	MAX
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
θ	10°	12°	14°